具有 Eco-Mode™ 的 4.5V 至 23V 输入，3A 同步降压 SWIFT™ 转换器

查询样片: TPS54339E

特性

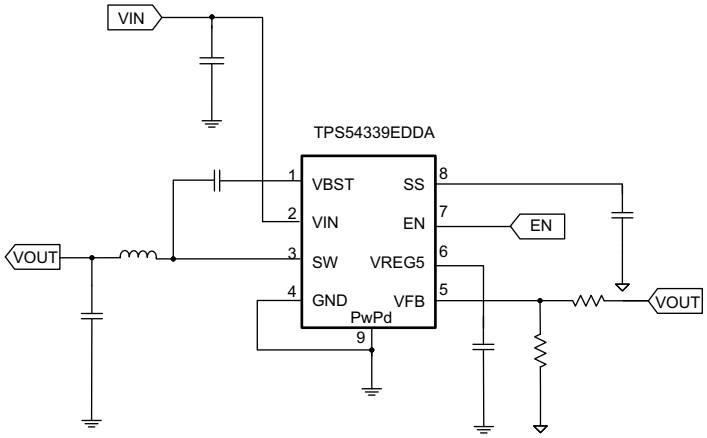
- **D-CAP2™** 模式支持快速瞬态响应
- 低输出纹波，支持陶瓷输出电容器
- 宽泛的 V_{IN} 输入电压范围：**4.5V** 至 **23V**
- 输出电压范围：**0.76V** 至 **7.0V**
- 高效率集成型场效应晶体管 **(FET)**
  针对更低占空比应用进行了优化
  -140mΩ（高侧）与 **70mΩ** （低侧）
- 高效率，关断时流耗少于 **10μA**
- 高初始带隙基准精度
- 可调软启动
- 预偏置软启动
- **600kHz** 开关频率 **(f_{SW})**
- 逐周期限流
- 自动跳跃 **Eco-mode™** 为了在轻负载下实现高效率

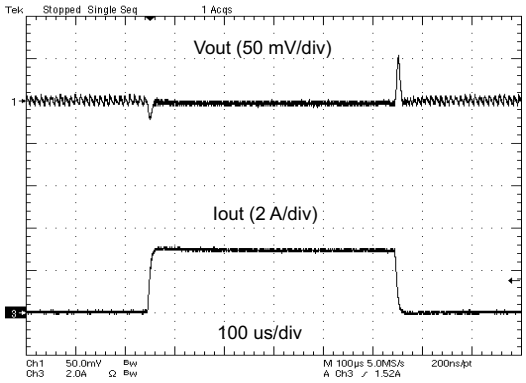
应用范围

- 低电压系统的广泛应用
  - 数字电视电源
  - 高清 **Blu-ray Disc™** 播放器
  - 网络家庭终端设备
  - 数字机顶盒 **(STB)**

说明

TPS54339E 是一款自适应接通时间 D-CAP2™ 模式同步降压转换器。 TPS54339E 可帮助系统设计人员通过一个低成本、低组件数、低待机电流解决方案来完成各种终端设备的电源总线调节器集。 TPS54339E 的主控制环路采用 D-CAP2™ 模式控制，无需外部补偿组件便可实现极快的瞬态响应。 自适应接通时间控制支持较高负载状态下的脉宽调制 (PWM) 模式与轻负载下的 Eco-mode™ 工作模式之间的无缝转换。 Eco-mode™ 使 TPS54339E 能够在较轻负载状况下保持高效率。 TPS54339E 的专有电路还有助于该器件适应诸如 POSCAP 或 SP-CAP 等低等效串联电阻 (ESR) 输出电容器以及超低 ESR 陶瓷电容器。 该器件的工作输入电压介于 4.5V 至 18V 之间。 输出电压可在 0.76V 与 7V 之间进行设定。此外，该器件还特有一个可调软启动时间。 TPS54339E 采用 8 引脚 DDA 封装，并针对 -40°C 到 85°C 的工作温度范围内的运行而设计。





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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION(1)

T_A	PACKAGE(2) (3)	ORDERABLE PART NUMBER	PIN	TRANSPORT MEDIA
–40°C to 85°C	DDA	TPS54339EDDA	8	Tube
		TPS54339EDDAR		Tape and Reel

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
(3) All package options have Cu NIPDAU lead/ball finish.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1)

		VALUE		UNIT
		MIN	MAX	
Input voltage range	VIN, EN	–0.3	25	V
	VBST	–0.3	31	
	VBST (10 ns transient)	–0.3	33	
	VBST (vs SW)	–0.3	6.5	
	VFB, SS	–0.3	6.5	
	SW	–2	25	
	SW (10 ns transient)	–3	27	
Output voltage range	VREG5	–0.3	6.5	V
	GND	–0.3	0.3	
Voltage from GND to thermal pad, V_{diff}		–0.2	0.2	V
Electrostatic discharge	Human Body Model (HBM)		2	kV
	Charged Device Model (CDM)		500	V
Operating junction temperature, T_J		–40	150	°C
Storage temperature, T_{stg}		–55	150	

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL INFORMATION

THERMAL METRIC(1)		TPS54339E DDA (8 PINS)	UNITS
θ_{JA}	Junction-to-ambient thermal resistance	46.2	°C/W
θ_{JCtop}	Junction-to-case (top) thermal resistance	53.9	
θ_{JB}	Junction-to-board thermal resistance	29.7	
ψ_{JT}	Junction-to-top characterization parameter	10.0	
ψ_{JB}	Junction-to-board characterization parameter	29.6	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	6.6	

(1) 有关传统和新的热 度量的更多信息，请参阅*IC 封装热度量*应用报告， SPRA953。

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RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range, (unless otherwise noted)

			MIN	MAX	UNIT
V_{IN}	Supply input voltage range		4.5	23	V
V_I	Input voltage range	VBST	–0.1	29	V
		VBST (10 ns transient)	–0.1	32	
		VBST(vs SW)	–0.1	5.7	
		SS	–0.1	5.7	
		EN	–0.1	23	
		VFB	–0.1	5.5	
		SW	–1.8	23	
		SW (10 ns transient)	–3	26	
		GND	–0.1	0.1	
V_O	Output voltage range	VREG5	–0.1	5.7	V
I_O	Output Current range	I_{VREG5}	0	10	mA
T_A	Operating free-air temperature		–40	85	°C
T_J	Operating junction temperature		–40	150	°C

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range, V_{IN} = 12 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY CURRENT						
I_{VIN}	Operating - non-switching supply current	V_{IN} current, T_A = 25°C, EN = 5V, V_{FB} = 0.8V		600	1100	µA
I_{VINSDN}	Shutdown supply current	V_{IN} current, T_A = 25°C, EN = 0 V		3.0	10	µA
LOGIC THRESHOLD						
V_{ENH}	EN high-level input voltage	EN	1.6			V
V_{ENL}	EN low-level input voltage	EN			0.6	V
R_{EN}	EN pin resistance to GND	V_{EN} = 12 V	200	400	800	kΩ
V_{FB} VOLTAGE AND DISCHARGE RESISTANCE						
V_{FBTH}	V_{FB} threshold voltage	T_A = 25°C, V_O = 1.05 V, I_O = 10 mA, Eco-mode™ operation		772		mV
		T_A = 25°C, V_O = 1.05 V, continuous mode operation	749	765	781	mV
I_{VFB}	V_{FB} input current	V_{FB} = 0.8 V, T_A = 25°C		0	±0.1	µA
V_{REG5} OUTPUT						
V_{VREG5}	V_{REG5} output voltage	T_A = 25°C, 6.0 V < V_{IN} < 23 V, 0 < I_{VREG5} < 5 mA	5.2	5.5	5.7	V
I_{VREG5}	Output current	V_{IN} = 6 V, V_{REG5} = 4.0 V, T_A = 25°C	20			mA
MOSFET						
$R_{DS(on)h}$	High side switch resistance	25°C, V_{BST} - SW = 5.5 V(1)		140		mΩ
$R_{DS(on)l}$	Low side switch resistance	25°C(1)		70		mΩ
CURRENT LIMIT						
I_{ocl}	Current limit	L out = 2.2 µH(1)	3.5	4.1	5.7	A
THERMAL SHUTDOWN						
T_{SDN}	Thermal shutdown threshold	Shutdown temperature (1)		165		°C
		Hysteresis (1)		40		
ON-TIME TIMER CONTROL						
t_{ON}	On time	V_{IN} = 12 V, V_O = 1.05 V		160		ns
$t_{OFF(MIN)}$	Minimum off time	T_A = 25°C, V_{FB} = 0.7 V(1)		260	310	ns

(1) Not production tested.

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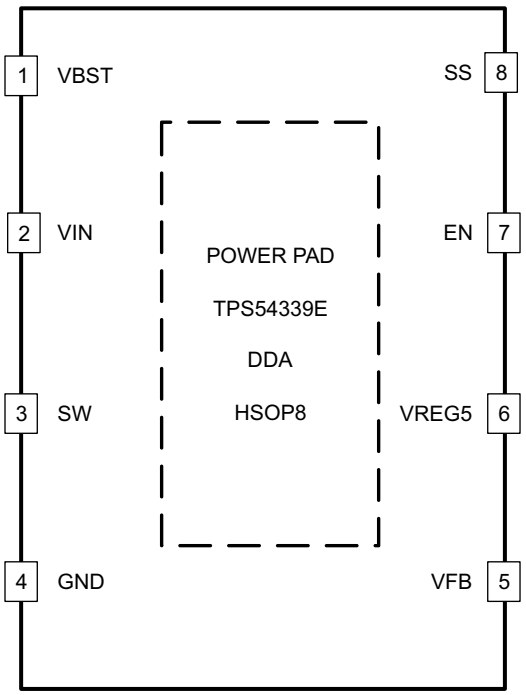
ELECTRICAL CHARACTERISTICS (continued)

over operating free-air temperature range, V_{IN} = 12 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SOFT START						
I_{SSC}	SS charge current	V_{SS} = 1.0 V	4.2	6.0	7.8	µA
I_{SSD}	SS discharge current	V_{SS} = 0.5 V	0.8	1.5		mA
HICCUP AND OVERVOLTAGE PROTECTION						
V_{OVP}	Output OVP threshold	OVP Detect (L>H)		125%		
V_{UVP}	Output Hiccup threshold	Hiccup detect (H>L)		65%		
T_{UVPDEL}	Output Hiccup delay	to Hiccup state		6		µs
T_{UVPEN}	Output Hiccup Enable delay	Relative to soft-start time		x1.7		
UVLO						
UVLO	UVLO threshold	Wake up V_{REG5} voltage	3.45	3.75	4.05	V
		Hysteresis V_{REG5} voltage	0.17	0.33	0.47	

DEVICE INFORMATION

DDA PACKAGE
(TOP VIEW)



PIN FUNCTIONS

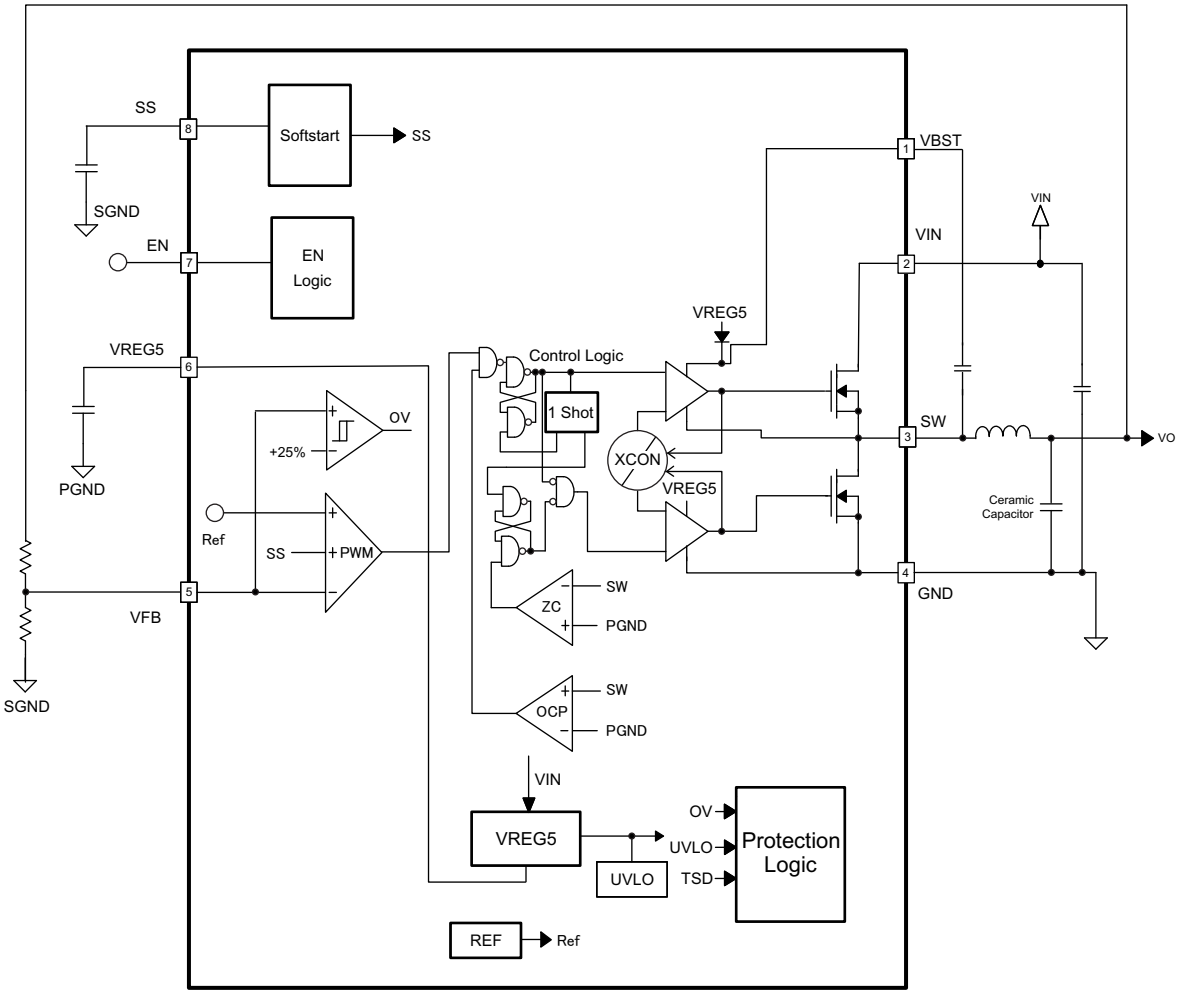
PIN		DESCRIPTION
NAME	NO.	
VBST	1	Supply input for the high-side FET gate drive circuit. Connect 0.1µF capacitor between VBST and SW pins. An internal diode is connected between VREG5 and VBST.
VIN	2	Input voltage supply pin.
SW	3	Switch node connection between high-side NFET and low-side NFET.
GND	4	Ground pin. Power ground return for switching circuit. Connect sensitive SS and VFB returns to GND at a single point.
VFB	5	Converter feedback input. Connect to output voltage with feedback resistor divider.

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PIN FUNCTIONS (continued)

PIN		DESCRIPTION
NAME	NO.	
VREG5	6	5.5 V power supply output. A capacitor (typical 0.47 µF) should be connected to GND. VREG5 is not active when EN is low.
EN	7	Enable input control. EN is active high and must be pulled up to enable the device.
SS	8	Soft-start control. An external capacitor should be connected to GND.
Exposed Thermal Pad	Back side	Thermal pad of the package. Must be soldered to achieve appropriate dissipation. Must be connected to GND.

FUNCTIONAL BLOCK DIAGRAM



OVERVIEW

The TPS54339E is a 3-A synchronous step-down (buck) converter with two integrated N-channel MOSFETs. It operates using D-CAP2™ mode control. The fast transient response of D-CAP2™ control reduces the output capacitance required to meet a specific level of performance. Proprietary internal circuitry allows the use of low ESR output capacitors including ceramic and special polymer types.

DETAILED DESCRIPTION

PWM Operation

The main control loop of the TPS54339E is an adaptive on-time pulse width modulation (PWM) controller that supports a proprietary D-CAP2™ mode control. D-CAP2™ mode control combines constant on-time control with an internal compensation circuit for pseudo-fixed frequency and low external component count configuration with both low ESR and ceramic output capacitors. It is stable even with virtually no ripple at the output.

At the beginning of each cycle, the high-side MOSFET is turned on. This MOSFET is turned off after internal one shot timer expires. This one shot is set by the converter input voltage, VIN, and the output voltage, VO, to maintain a pseudo-fixed frequency over the input voltage range, hence it is called adaptive on-time control. The one-shot timer is reset and the high-side MOSFET is turned on again when the feedback voltage falls below the reference voltage. An internal ramp is added to reference voltage to simulate output ripple, eliminating the need for ESR induced output ripple from D-CAP2™ mode control.

PWM Frequency and Adaptive On-Time Control

TPS54339E uses an adaptive on-time control scheme and does not have a dedicated on board oscillator. The TPS54339E runs with a pseudo-constant frequency of 600 kHz by using the input voltage and output voltage to set the on-time one-shot timer. The on-time is inversely proportional to the input voltage and proportional to the output voltage; therefore, when the duty ratio is VOUT/VIN, the frequency is constant.

Auto-Skip Eco-Mode™ Control

The TPS54339E is designed with Auto-Skip Eco-mode™ to increase light load efficiency. As the output current decreases from heavy load condition, the inductor current is also reduced and eventually comes to point that its rippled valley touches zero level, which is the boundary between continuous conduction and discontinuous conduction modes. The rectifying MOSFET is turned off when its zero inductor current is detected. As the load current further decreases the converter run into discontinuous conduction mode. The on-time is kept almost the same as is was in the continuous conduction mode so that it takes longer time to discharge the output capacitor with smaller load current to the level of the reference voltage. The transition point to the light load operation $I_{OUT(LL)}$ current can be calculated in Equation 1

$$I_{OUT(LL)} = \frac{1}{2 \cdot L \cdot fsw} \cdot \frac{(V_{IN} - V_{OUT}) \cdot V_{OUT}}{V_{IN}} \quad (1)$$

Soft Start and Pre-Biased Soft Start

The soft start function is adjustable. When the EN pin becomes high, 6 µA current begins charging the capacitor which is connected from the SS pin to GND. Smooth control of the output voltage is maintained during start up. The equation for the slow start time is shown in Equation 2. VFB voltage is 0.765 V and SS pin source current is 6 µA.

$$t_{SS}(ms) = \frac{C_{SS}(nF) \times V_{REF} \times 1.1}{I_{SS}(\mu A)} = \frac{C_{SS}(nF) \times 0.765 \times 1.1}{6} \quad (2)$$

The TPS54339E contains a unique circuit to prevent current from being pulled from the output during startup if the output is pre-biased. When the soft-start commands a voltage higher than the pre-bias level (internal soft start becomes greater than feedback voltage V_{FB}), the controller slowly activates synchronous rectification by starting the first low side FET gate driver pulses with a narrow on-time. It then increments that on-time on a cycle-by-cycle basis until it coincides with the time dictated by (1-D), where D is the duty cycle of the converter. This scheme prevents the initial sinking of the pre-bias output, and ensure that the out voltage (V_O) starts and ramps up smoothly into regulation and the control loop is given time to transition from pre-biased start-up to normal mode operation.

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Current Protection

The output overcurrent protection (OCP) is implemented using a cycle-by-cycle valley detect control circuit. The switch current is monitored by measuring the low-side FET switch voltage between the SW pin and GND. This voltage is proportional to the switch current. To improve accuracy, the voltage sensing is temperature compensated.

During the on time of the high-side FET switch, the switch current increases at a linear rate determined by V_{IN}, V_{OUT}, the on-time and the output inductor value. During the on time of the low-side FET switch, this current decreases linearly. The average value of the switch current is the load current Iout. The TPS54339E constantly monitors the low-side FET switch voltage, which is proportional to the switch current, during the low-side on-time. If the measured voltage is above the voltage proportional to the current limit, an internal counter is incremented per each SW cycle and the converter maintains the low-side switch on until the measured voltage is below the voltage corresponding to the current limit at which time the switching cycle is terminated and a new switching cycle begins. In subsequent switching cycles, the on-time is set to a fixed value and the current is monitored in the same manner. If the over current condition exists for 7 consecutive switching cycles, the internal OCL threshold is set to a lower level, reducing the available output current. When a switching cycle occurs where the switch current is not above the lower OCL threshold, the counter is reset and the OCL limit is returned to the higher value.

There are some important considerations for this type of over-current protection. The load current one half of the peak-to-peak inductor current higher than the over-current threshold. Also when the current is being limited, the output voltage tends to fall as the demanded load current may be higher than the current available from the converter. This may cause the output voltage to fall. When the VFB voltage becomes lower than 65% of the target voltage, the UVP comparator detects it. After 6μs detecting the UVP voltage, device will shut down and re-start after 7 times SS period for Hiccup.

When the over current condition is removed, the output voltage returns to the regulated value. This protection is non-latching.

Over Voltage Protection

TPS54339E detects over voltage conditions by monitoring the feedback voltage (VFB). This function is enabled after approximately 1.7 x times the soft start time.

When the feedback voltage becomes higher than 125% of the target voltage, the OVP comparator output goes high and both the high-side MOSFET driver and the low-side MOSFET driver turn off. This function is non-latch operation.

UVLO Protection

Undervoltage lock out protection (UVLO) monitors the voltage of the V_{REG5} pin. When the V_{REG5} voltage is lower than UVLO threshold voltage, the TPS54339E is shut off. This protection is non-latching.

Thermal Shutdown

TPS54339E monitors the temperature of itself. If the temperature exceeds the threshold value (typically 165°C), the device is shut off. This is non-latch protection.

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TYPICAL CHARACTERISTICS

VIN = 12 V, T_A = 25°C (unless otherwise noted).

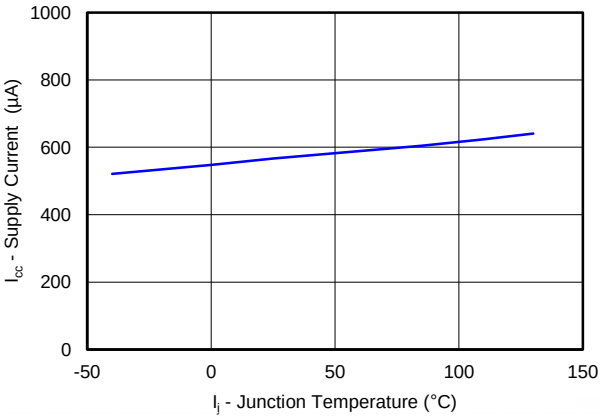


Figure 1. VIN CURRENT vs JUNCTION TEMPERATURE

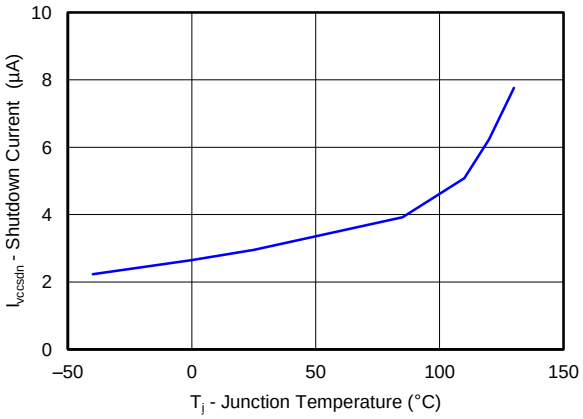


Figure 2. VIN SHUTDOWN CURRENT vs JUNCTION TEMPERATURE

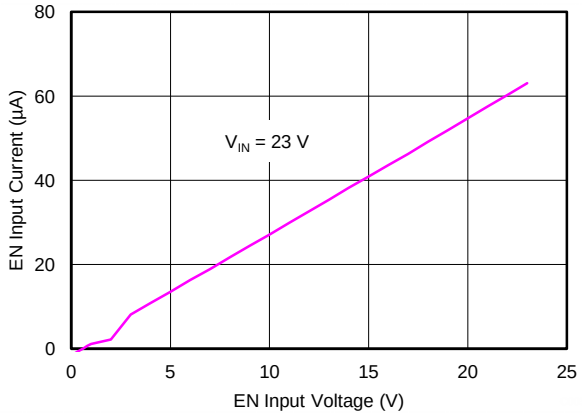


Figure 3. EN CURRENT vs EN VOLTAGE

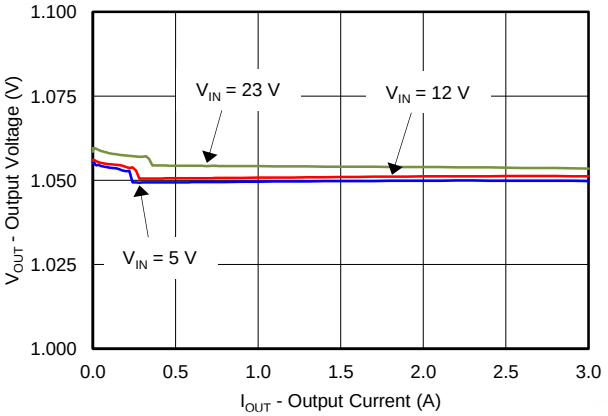


Figure 4. 1.05-V OUTPUT VOLTAGE vs OUTPUT CURRENT

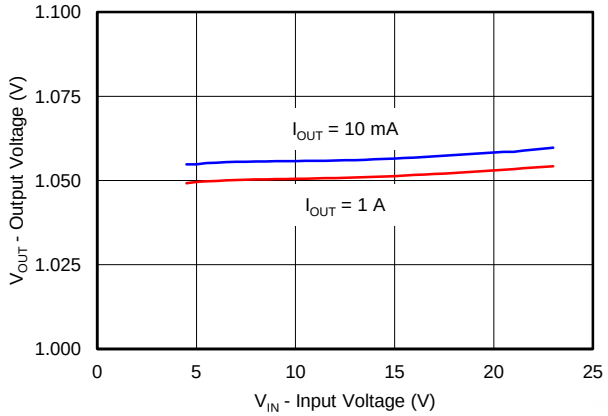


Figure 5. 1.05-V OUTPUT VOLTAGE vs INPUT VOLTAGE

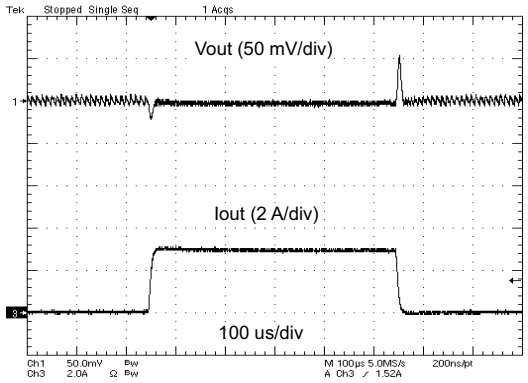


Figure 6. 1.05-V, LOAD TRANSIENT RESPONSE

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TYPICAL CHARACTERISTICS

VIN = 12 V, T_A = 25°C (unless otherwise noted).

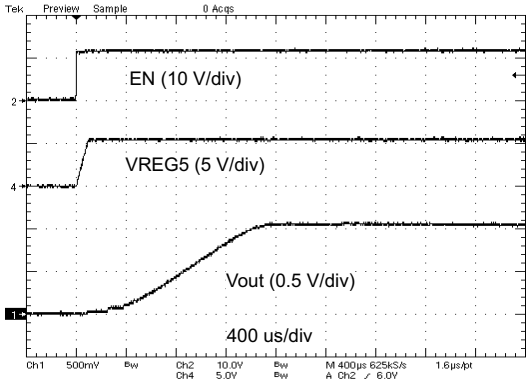


Figure 7. START-UP WAVE FORM

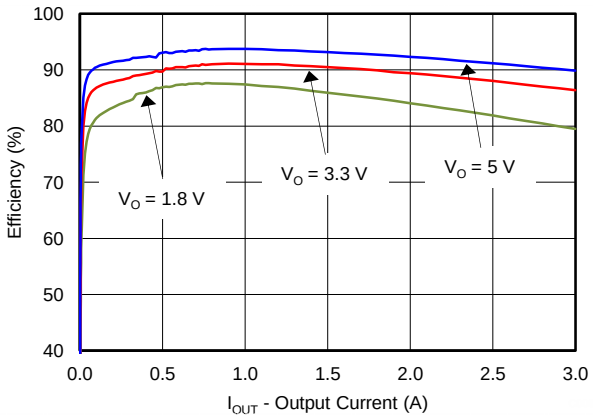


Figure 8. EFFICIENCY vs OUTPUT CURRENT

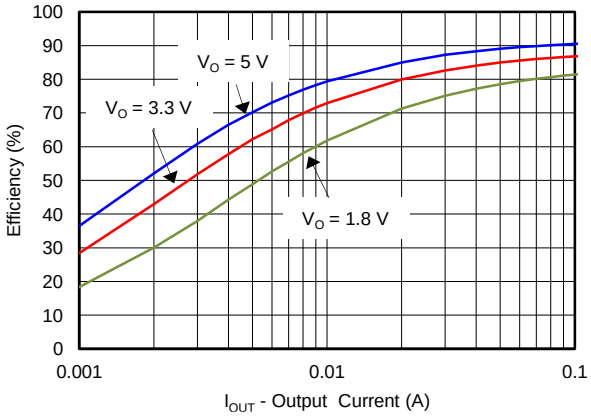


Figure 9. LIGHT LOAD EFFICIENCY vs OUTPUT CURRENT

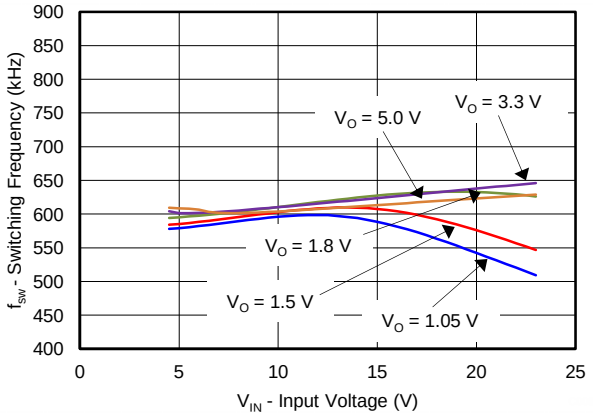


Figure 10. SWITCHING FREQUENCY vs INPUT VOLTAGE (I_O = 1 A)

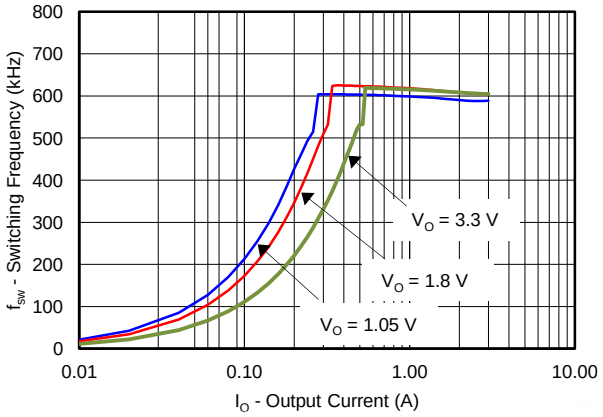


Figure 11. SWITCHING FREQUENCY vs OUTPUT CURRENT

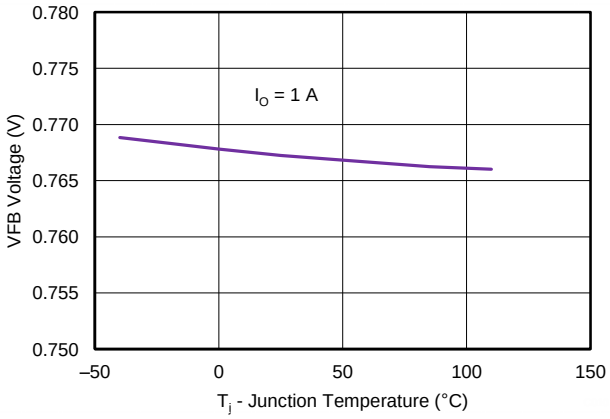


Figure 12. VFB VOLTAGE vs JUNCTION TEMPERATURE (I_O = 1 A)

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TYPICAL CHARACTERISTICS (continued)

VIN = 12 V, T_A = 25°C (unless otherwise noted).

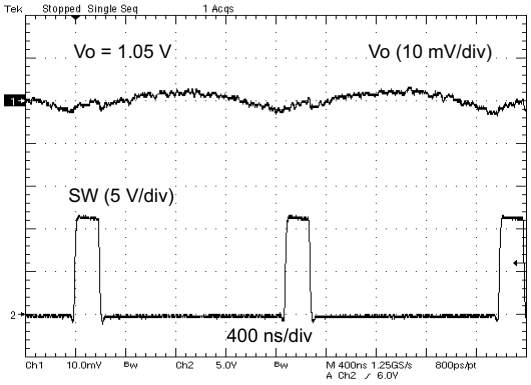


Figure 13. VOLTAGE RIPPLE AT OUTPUT (I_O = 3A)

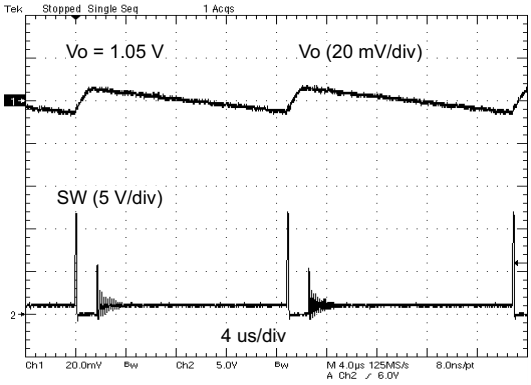


Figure 14. VOLTAGE RIPPLE AT OUTPUT (I_O = 30 mA)

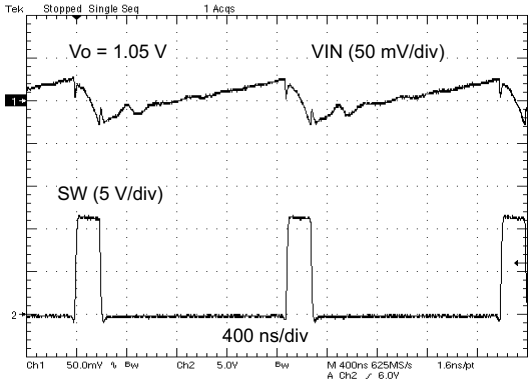


Figure 15. VOLTAGE RIPPLE AT INPUT (I_O = 3 A)

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DESIGN GUIDE

Step-By-Step Design Procedure

To begin the design process, the user must know a few application parameters:

- Input voltage range
- Output voltage
- Output current
- Output voltage ripple
- Input voltage ripple

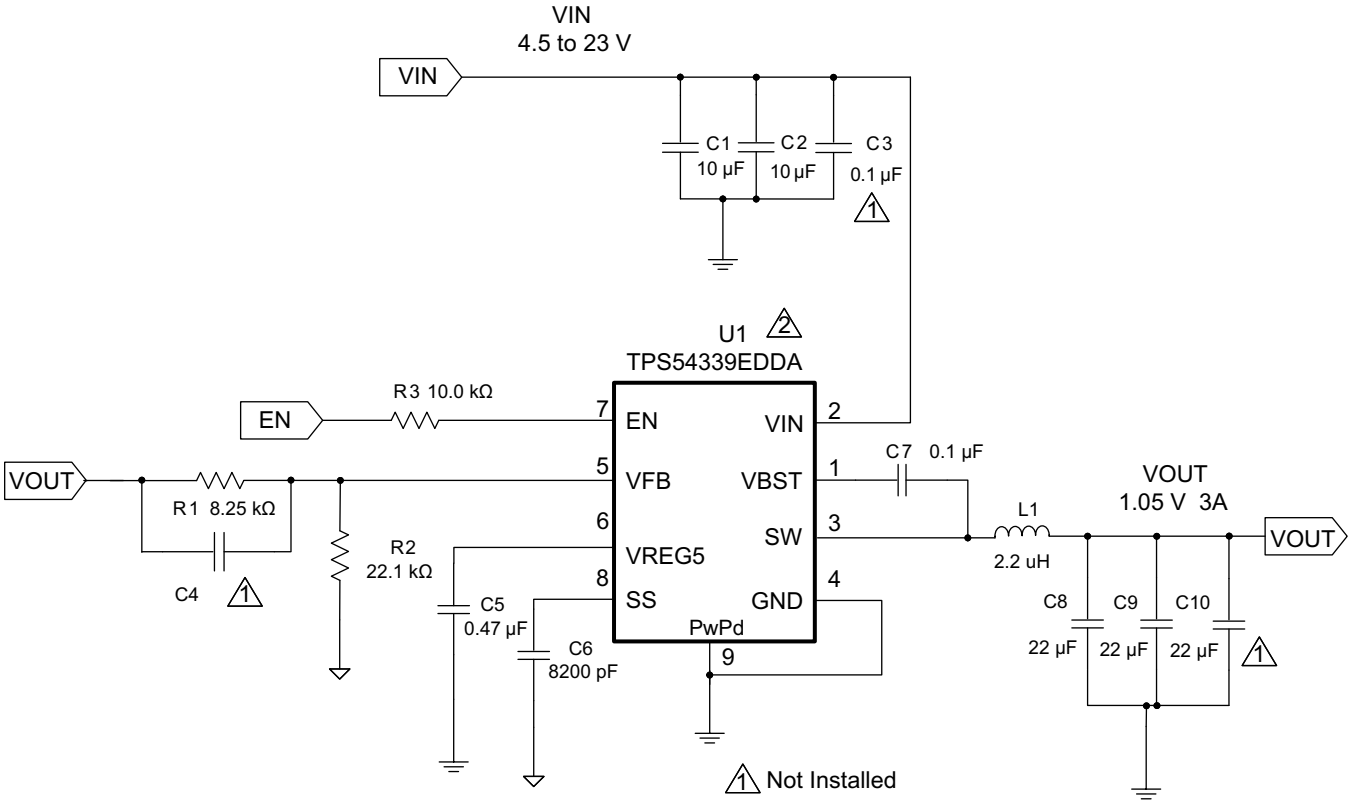


Figure 16. Shows the schematic diagram for this design example.

Output Voltage Resistors Selection

The output voltage is set with a resistor divider from the output node to the VFB pin. It is recommended to use 1% tolerance or better divider resistors. Start by using Equation 3 to calculate V_{OUT}.

To improve efficiency at light loads consider using larger value resistors, high resistance is more susceptible to noise, and the voltage errors from the VFB input current are more noticeable.

$$V_{OUT} = 0.765 \times \left(1 + \frac{R1}{R2}\right) \quad (3)$$

Output Filter Selection

The output filter used with the TPS54339E is an LC circuit. This LC filter has double pole at:

$$F_P = \frac{1}{2\pi\sqrt{L_{OUT} \times C_{OUT}}} \quad (4)$$

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At low frequencies, the overall loop gain is set by the output set-point resistor divider network and the internal gain of the TPS54339E. The low frequency phase is 180 degrees. At the output filter pole frequency, the gain rolls off at a –40 dB per decade rate and the phase drops rapidly. D-CAP2™ introduces a high frequency zero that reduces the gain roll off to –20 dB per decade and increases the phase to 90 degrees one decade above the zero frequency. The inductor and capacitor selected for the output filter must be selected so that the double pole of Equation 4 is located below the high frequency zero but close enough that the phase boost provided be the high frequency zero provides adequate phase margin for a stable circuit. To meet this requirement use the values recommended in Table 1

Table 1. Recommended Component Values

Output Voltage (V)	R1 (kΩ)	R2 (kΩ)	C4 (pF)(1)			L1 (µH)			C8 + C9 (µF)	
			Min	Typ	Max	Min	Typ	Max	Min	Max
1	6.81	22.1	5	150	220	1.5	2.2	4.7	22	68
1.05	8.25	22.1	5	150	220	1.5	2.2	4.7	22	68
1.2	12.7	22.1	5		100	1.5	2.2	4.7	22	68
1.5	21.5	22.1	5		68	1.5	2.2	4.7	22	68
1.8	30.1	22.1	5		22	2.2	3.3	4.7	22	68
2.5	49.9	22.1	5		22	2.2	3.3	4.7	22	68
3.3	73.2	22.1	5		22	2.2	3.3	4.7	22	68
5	124	22.1	5		22	3.3		4.7	22	68
6.5	165	22.1	5		22	3.3		4.7	22	68

(1) Optional

Since the DC gain is dependent on the output voltage, the required inductor value increases as the output voltage increases. Additional phase boost can be achieved by adding a feed forward capacitor (C4) in parallel with R1. The amount of available phase boost is dependent on the output voltage. Higher output voltages will allow greater phase boost.

The inductor peak-to-peak ripple current, peak current and RMS current are calculated using Equation 5, Equation 6 and Equation 7. The inductor saturation current rating must be greater than the calculated peak current and the RMS or heating current rating must be greater than the calculated RMS current. Use 600 kHz for f_{SW}.

Use 600 kHz for f_{SW}. Make sure the chosen inductor is rated for the peak current of Equation 6 and the RMS current of Equation 7.

$$II_{P-P} = \frac{V_{OUT}}{V_{IN(MAX)}} \times \frac{V_{IN(MAX)} - V_{OUT}}{L_O \times f_{SW}} \quad (5)$$

$$II_{PEAK} = I_O + \frac{II_{P-P}}{2} \quad (6)$$

$$I_{LO(RMS)} = \sqrt{I_O^2 + \frac{1}{12} II_{P-P}^2} \quad (7)$$

For this design example, the calculated peak current is 3.36 A and the calculated RMS current is 3.01 A. The inductor used is a TDK CLF7045T-2R2N with a peak current rating of 5.5 A and an RMS current rating of 4.3 A. For high current designs, TDK SPM6530T-4R7M 4.7µH is also recommended. The SPM6530 series has a higher current rating than the CLF7045 series.

The capacitor value and ESR determines the amount of output voltage ripple. The TPS54339E is intended for use with ceramic or other low ESR capacitors. Recommended values range from 22µF to 68µF. Use Equation 8 to determine the required RMS current rating for the output capacitor.

$$I_{Co(RMS)} = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{\sqrt{12} \times V_{IN} \times L_O \times f_{SW}} \quad (8)$$

For this design two TDK C3216X5R0J226M 22µF output capacitors are used. The typical ESR is 2 mΩ each. The calculated RMS current is 0.21 A and each output capacitor is rated for 4A.

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Input Capacitor Selection

The TPS54339E requires an input decoupling capacitor and a bulk capacitor is needed depending on the application. A ceramic capacitor over 10 µF is recommended for the decoupling capacitor. An additional 0.1 µF capacitor from pin 2 to ground is optional to provide additional high frequency filtering. The capacitor voltage rating needs to be greater than the maximum input voltage.

Bootstrap Capacitor Selection

A 0.1 µF. ceramic capacitor must be connected between the VBST to SW pin for proper operation. It is recommended to use a ceramic capacitor.

VREG5 Capacitor Selection

A 0.47 µF. ceramic capacitor must be connected between the VREG5 to GND pin for proper operation. It is recommended to use a ceramic capacitor.

THERMAL INFORMATION

This 8-pin DDA package incorporates an exposed thermal pad that is designed to be directly to an external heartsick. The thermal pad must be soldered directly to the printed board (PCB). After soldering, the PCB can be used as a heartsick. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heartsick structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the exposed thermal pad and how to use the advantage of its heat dissipating abilities, see the Technical Brief, PowerPAD™ Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD™ Made Easy, Texas Instruments Literature No. SLMA004.

The exposed thermal pad dimensions for this package are shown in the following illustration.

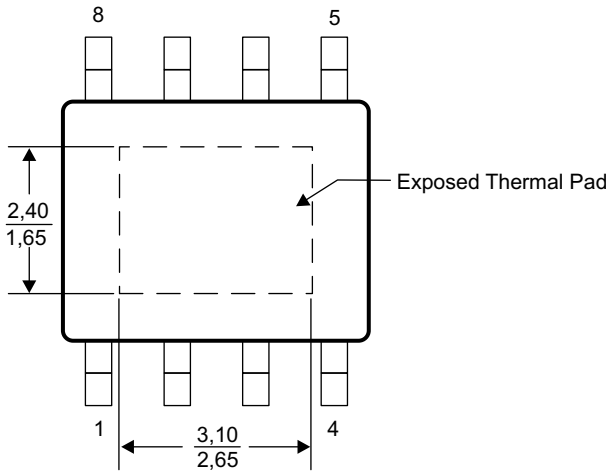


Figure 17. Thermal Pad Dimensions

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LAYOUT CONSIDERATIONS

1. Keep the input switching current loop as small as possible.
2. Keep the SW node as physically small and short as possible to minimize parasitic capacitance and inductance and to minimize radiated emissions. Kelvin connections should be brought from the output to the feedback pin of the device.
3. Keep analog and non-switching components away from switching components.
4. Make a single point connection from the analog ground to power ground.
5. Do not allow switching current to flow under the device.
6. Keep the pattern lines for VIN and PGND broad.
7. Exposed pad of device must be connected to PGND with solder.
8. VREG5 capacitor should be placed near the device, and connected to PGND.
9. Output capacitor should be connected to a broad pattern of the PGND.
10. Voltage feedback loop should be as short as possible, and preferably with ground shield.
11. Lower resistor of the voltage divider which is connected to the VFB pin should be tied to analog ground trace.
12. Providing sufficient via is preferable for VIN, SW and PGND connection.
13. VIN input bypass capacitor and VIN high frequency bypass capacitor must be placed as near as possible to the device.
14. Performance based on four layer printed circuit board.

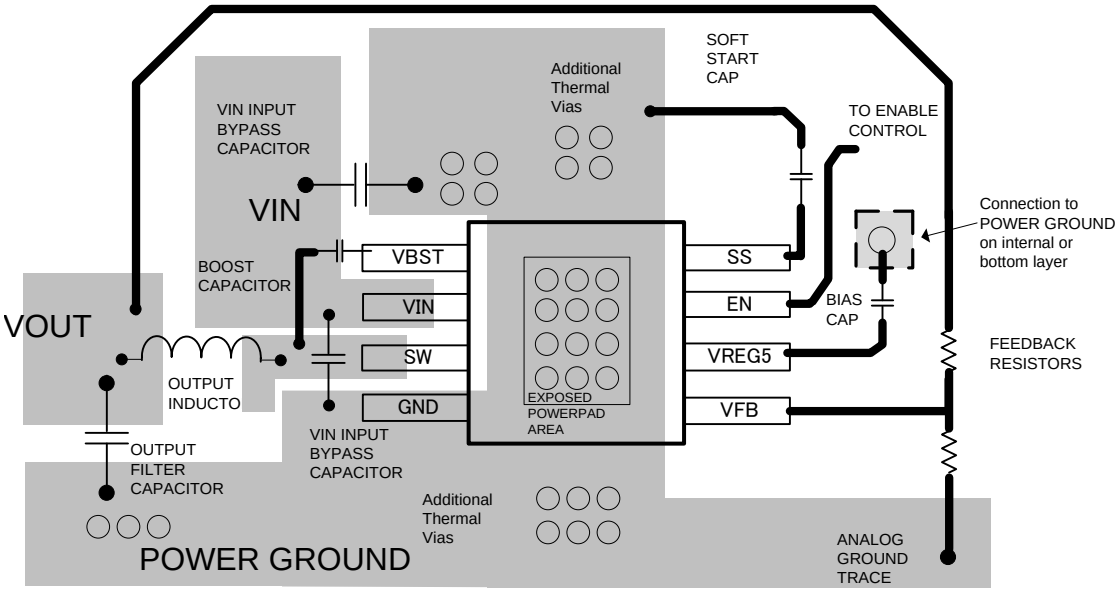


Figure 18. PCB Layout

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS54339EDDA	Active	Production	SO PowerPAD (DDA) | 8	75 | TUBE	Yes	NIPDAU | SN	Level-2-260C-1 YEAR	-40 to 85	54339E
TPS54339EDDA.A	Active	Production	SO PowerPAD (DDA) | 8	75 | TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	54339E
TPS54339EDDAR	Active	Production	SO PowerPAD (DDA) | 8	2500 | LARGE T&R	Yes	NIPDAU | SN	Level-2-260C-1 YEAR	-40 to 85	54339E
TPS54339EDDAR.A	Active	Production	SO PowerPAD (DDA) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	54339E

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

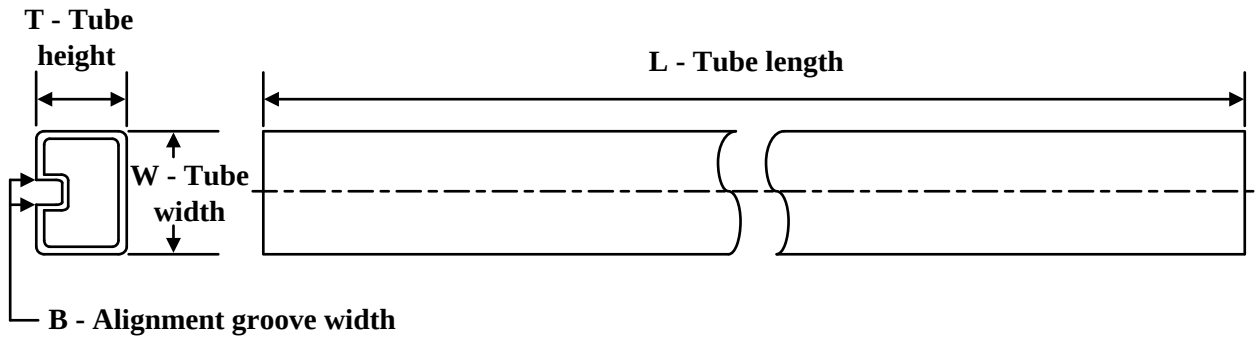
(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TUBE

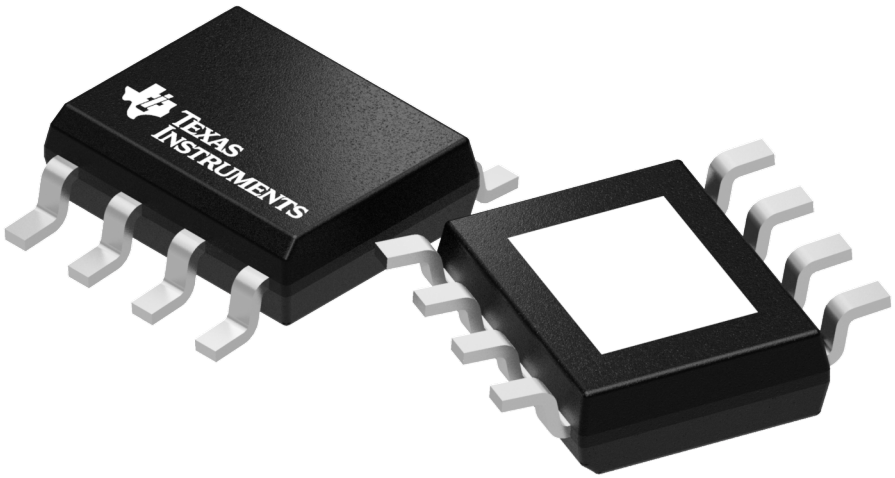


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TPS54339EDDA	DDA	HSOIC	8	75	507	8	3940	4.32
TPS54339EDDA	DDA	HSOIC	8	75	517	7.87	635	4.25
TPS54339EDDA.A	DDA	HSOIC	8	75	507	8	3940	4.32
TPS54339EDDA.A	DDA	HSOIC	8	75	517	7.87	635	4.25

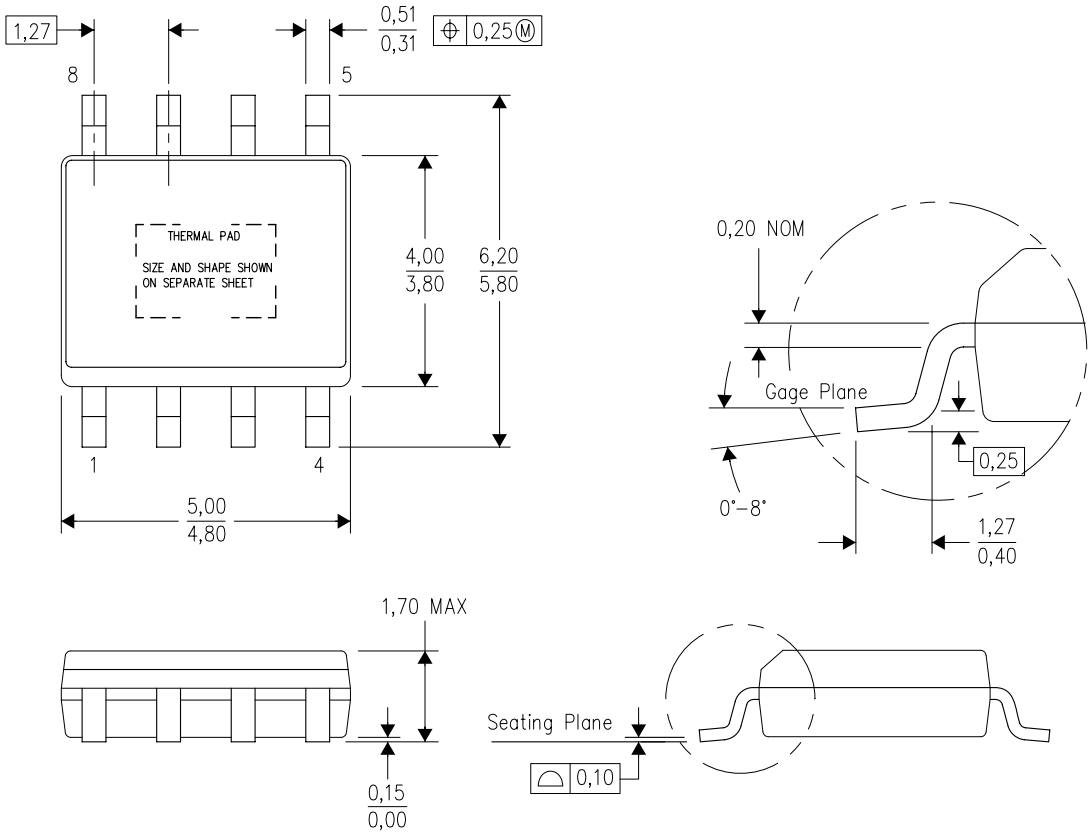
DDA 8 PowerPAD™ SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

DDA (R–PDSO–G8) PowerPAD™ PLASTIC SMALL–OUTLINE



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <http://www.ti.com>.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. This package complies to JEDEC MS–012 variation BA

PowerPAD is a trademark of Texas Instruments.

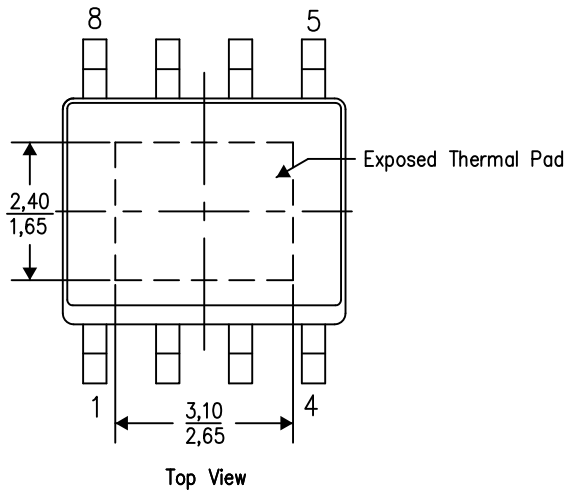
DDA (R–PDSO–G8) PowerPAD™ PLASTIC SMALL OUTLINE

THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



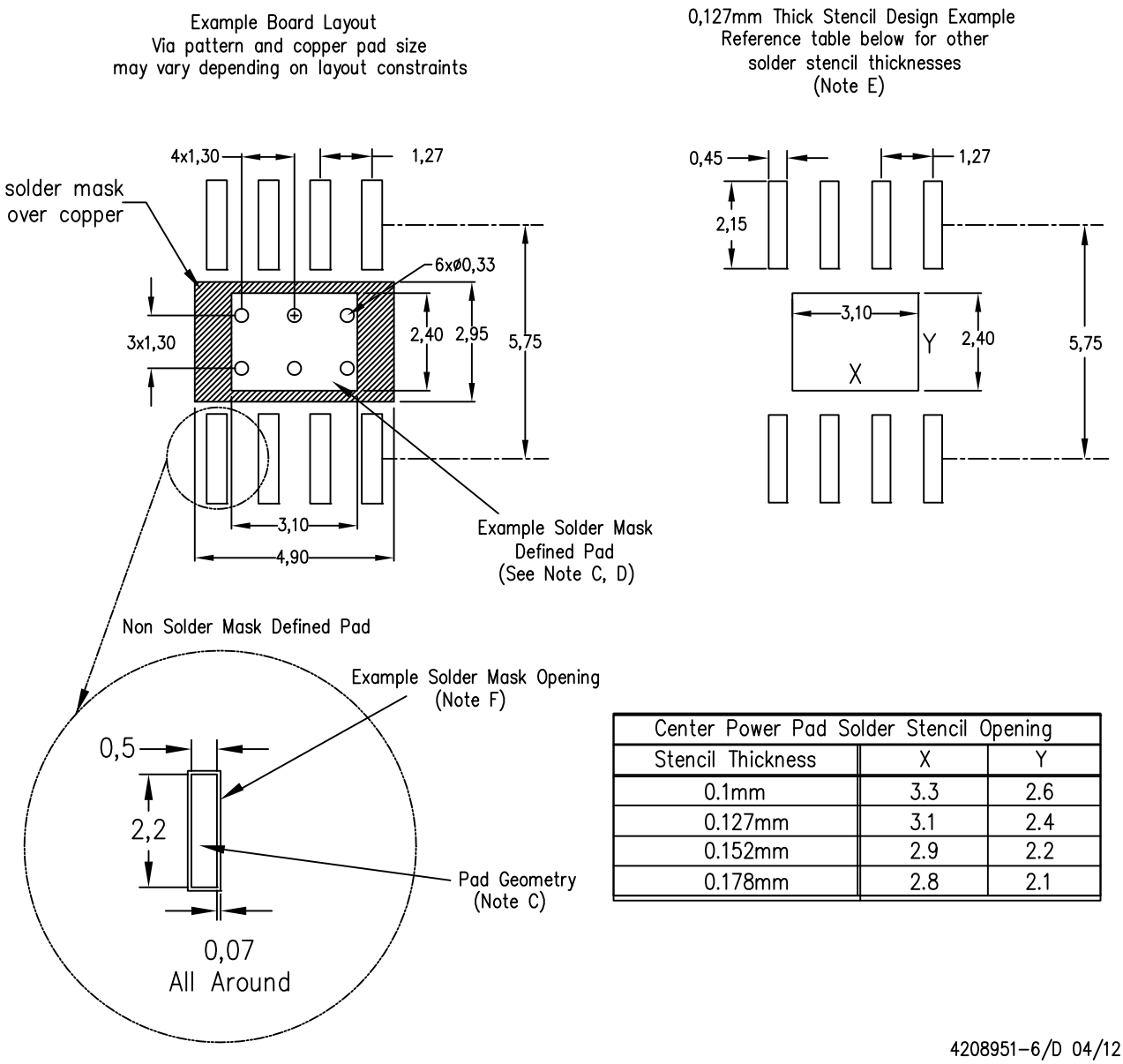
Exposed Thermal Pad Dimensions

4206322–6/L 05/12

NOTE: A. All linear dimensions are in millimeters

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DDA (R–PDSO–G8) PowerPAD™ PLASTIC SMALL OUTLINE



Center Power Pad Solder Stencil Opening		
Stencil Thickness	X	Y
0.1mm	3.3	2.6
0.127mm	3.1	2.4
0.152mm	2.9	2.2
0.178mm	2.8	2.1

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.
F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

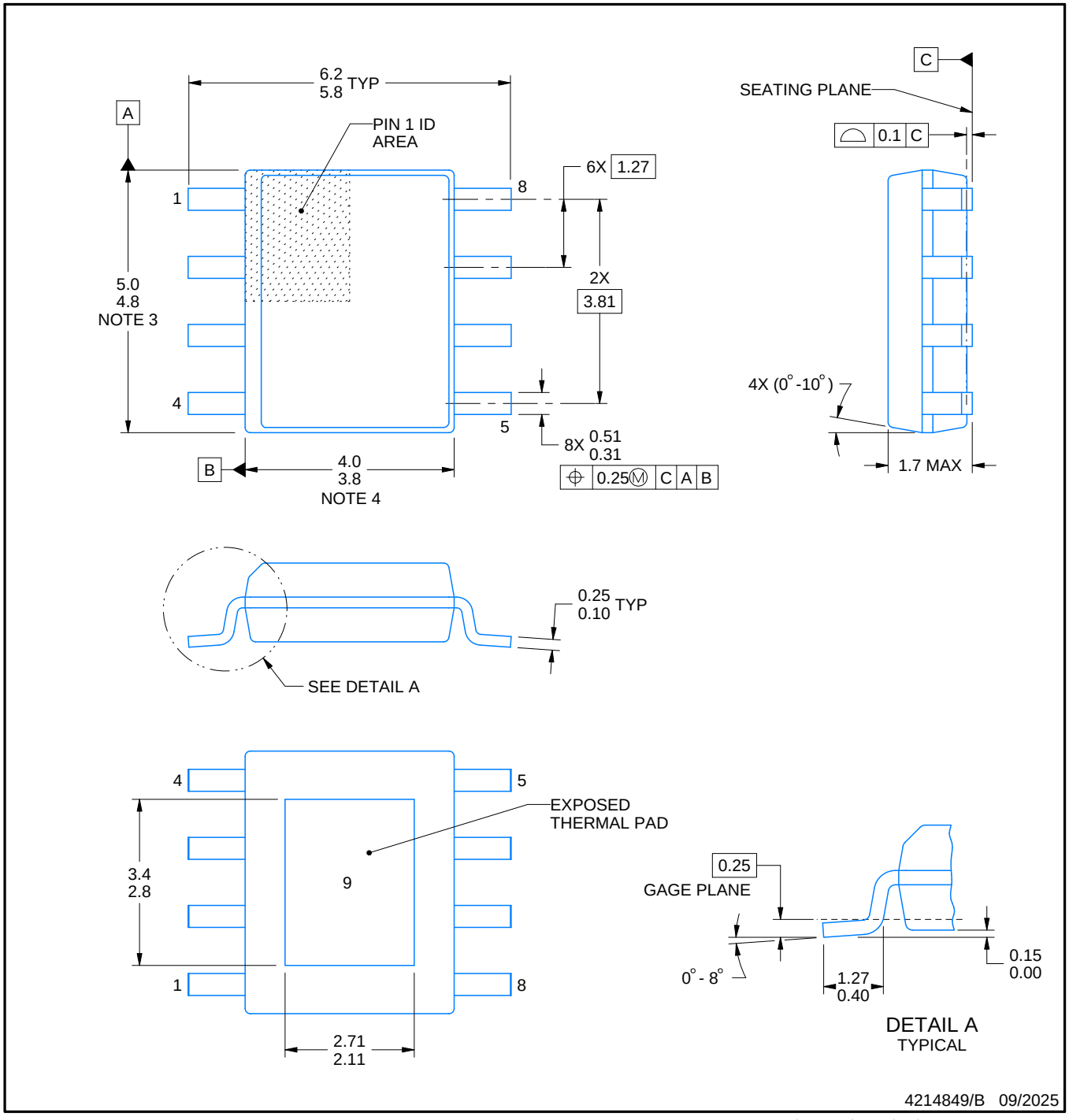
PowerPAD is a trademark of Texas Instruments.

PACKAGE OUTLINE

DDA0008B

PowerPAD™ SOIC - 1.7 mm max height

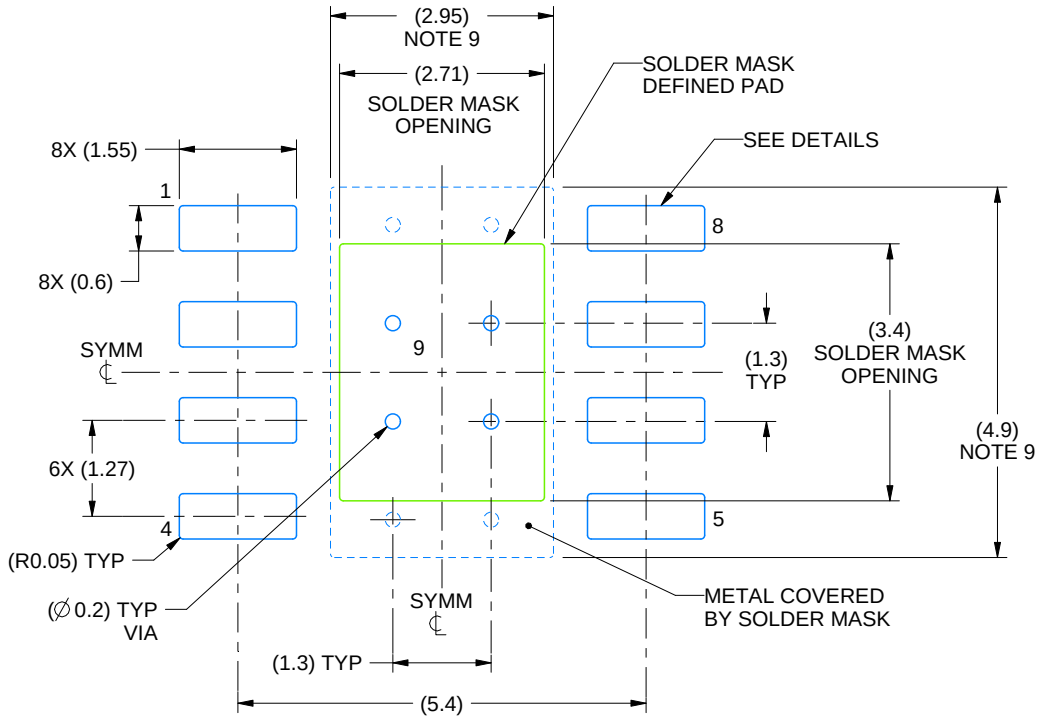
PLASTIC SMALL OUTLINE



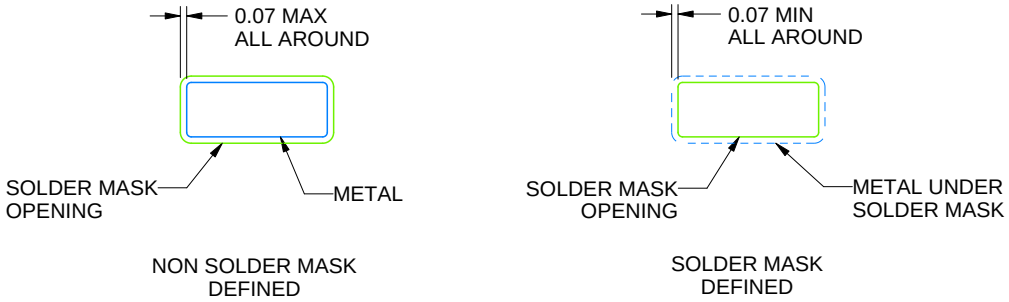
PowerPAD is a trademark of Texas Instruments.

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MS-012.



LAND PATTERN EXAMPLE
SCALE:10X



SOLDER MASK DETAILS
PADS 1-8

4214849/B 09/2025

NOTES: (continued)

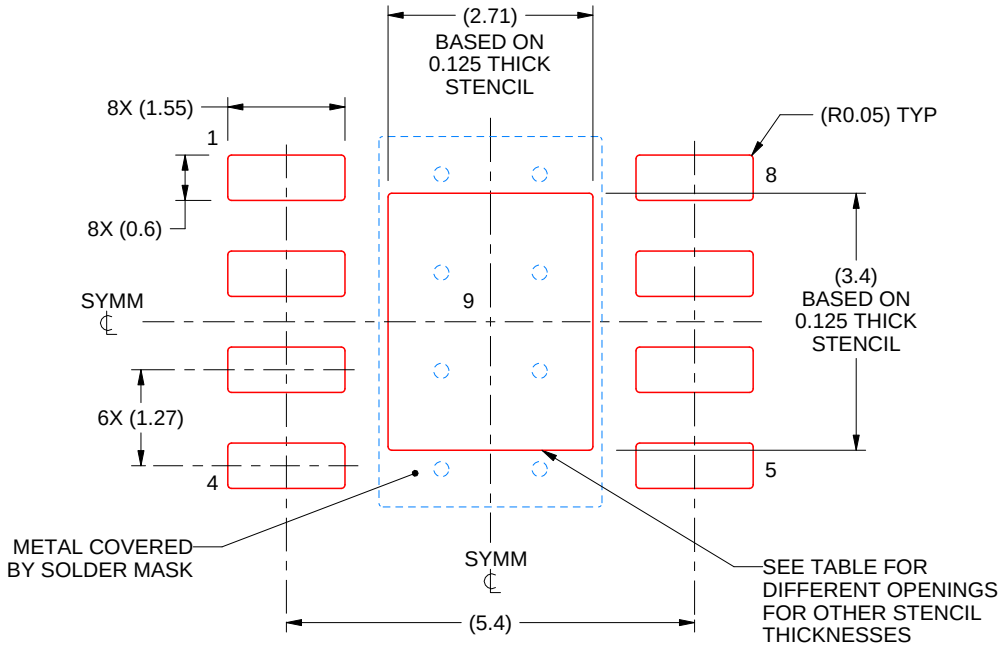
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
9. Size of metal pad may vary due to creepage requirement.
10. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DDA0008B

PowerPAD™ SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
EXPOSED PAD
100% PRINTED SOLDER COVERAGE BY AREA
SCALE:10X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	3.03 X 3.80
0.125	2.71 X 3.40 (SHOWN)
0.150	2.47 X 3.10
0.175	2.29 X 2.87

4214849/B 09/2025

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

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最后更新日期：2025 年 10 月